

L Number	Hits	Search Text	DB	Time stamp
1	1	("5581115").PN.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 15:16
-	0	("Sicsiliconadjcarbide").PN.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/01 16:55
-	76801	Sic silicon adj carbide	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:32
-	423	(bipolar bjt hbt hbjt) and base with doped near5 contact and base with (opening hole recess)	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:31
-	22	(Sic silicon adj carbide) and ((bipolar bjt hbt hbjt) and base with doped near5 contact and base with (opening hole recess))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:32
-	4	("4945394" "5319220" "5641975" "5847414").PN.	USPAT	2004/05/01 17:18
-	25	4945394.URPN.	USPAT	2004/05/01 17:23
-	8	("4945394" "5318915" "5424227" "5539217" "5726463" "5798277" "5814859" "6143593").PN.	USPAT	2004/05/01 17:25
-	1	("6194769").PN.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 11:24
-	4	((6,218,254) or (5,980,265) or (5,409,859) or (5,296,391)).PN.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:10
-	3	((5,914,611) or (6,228,665) or (6218254)).PN.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:10
-	7	("4945394" "5318915" "5539217" "5726463" "5798277" "5814859" "6143593").PN.	USPAT	2004/05/04 12:11
-	25	4945394.URPN.	USPAT	2004/05/04 12:14
-	8	5350699.URPN.	USPAT	2004/05/04 12:18
-	781	(bipolar bjt hbt hbjt) and base with doped near5 contact	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 09:30
-	76866	Sic silicon adj carbide	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:32
-	54	((bipolar bjt hbt hbjt) and base with doped near5 contact) and (Sic silicon adj carbide)	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:43
-	22	(Sic silicon adj carbide) and ((bipolar bjt hbt hbjt) and base with doped near5 contact and base with (opening hole recess))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 12:33
-	32	((bipolar bjt hbt hbjt) and base with doped near5 contact) and (Sic silicon adj carbide) not ((Sic silicon adj carbide) and ((bipolar bjt hbt hbjt) and base with doped near5 contact and base with (opening hole recess)))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:42

-	3	("5332912" "5767540" "6313488").PN.	USPAT	2004/05/04 12:36
-	33	((bipolar bjt hbt hbjt) and base with doped near5 contact) and (Sic sigec sicge gesic gecsi csige cgesi silicon near3 carbide)) not ((Sic silicon adj carbide) and ((bipolar bjt hbt hbjt) and base with doped near5 contact and base with (opening hole recess)))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:46
-	54	((bipolar bjt hbt hbjt) and base with doped near5 contact) and (Sic silicon adj carbide)	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:44
-	1	((bipolar bjt hbt hbjt) and base with doped near5 contact) and (Sic sigec sicge gesic gecsi csige cgesi silicon near3 carbide) not (Sic silicon adj carbide)	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:45
-	55	((bipolar bjt hbt hbjt) and base with doped near5 contact) and (Sic sigec sicge gesic gecsi csige cgesi silicon near3 carbide)	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 14:46
-	1	((bipolar bjt hbt hbjt) and base with doped near5 contact) and (Sic sigec sicge gesic gecsi csige cgesi silicon near3 carbide) not (((bipolar bjt hbt hbjt) and base with doped near5 contact) and (Sic silicon adj carbide))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 17:25
-	374	((bipolar bjt hbt hbjt) and base near5 (heavily highly) adj doped and base with (opening etch\$ hole recess\$))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 17:28
-	74	(bipolar bjt hbt hbjt) and base near5 (heavily highly) adj doped and base with (opening etch\$ hole recess\$) and (sic compound adj semiconductor)	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 17:29
-	43	(bipolar bjt hbt hbjt) and base near5 (heavily highly) adj doped and base with (opening etch\$ hole recess\$) and (sic silicon near2 carbide)	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/04 18:20
-	36	((bipolar bjt hbt hbjt) and base near5 (heavily highly) adj doped and base with (opening etch\$ hole recess\$) and (sic compound adj semiconductor)) not ((bipolar bjt hbt hbjt) and base near5 (heavily highly) adj doped and base with (opening etch\$ hole recess\$) and (sic silicon near2 carbide))	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/05 16:24
-	1	i21 and sic	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/05 16:24
-	177	i21	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 09:10
-	30	(Kordesch-martins\$ Bartlow-Howard\$ Woodin-Richard\$).in.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 09:16
-	379	(fairchild).as. and active	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 09:17
-	891	(fairchild).as. and semiconductor	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 09:17

-	1	("20030039012").PN.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB USPAT; US_PGPUB; EPO; JPO; IBM_TDB USPAT; US_PGPUB; EPO; JPO; IBM_TDB USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 13:25
-	1	("20010043663").PN.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB USPAT; US_PGPUB; EPO; JPO; IBM_TDB USPAT; US_PGPUB; EPO; JPO; IBM_TDB USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 13:18
-	1	("20010030818").PN.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB USPAT; US_PGPUB; EPO; JPO; IBM_TDB USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 13:18
-	1	("20030206686").PN.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 13:18
-	1	("20030210448").PN.	USPAT; US_PGPUB; EPO; JPO; IBM_TDB	2004/05/08 15:16